SM7A22NSF/SM7A22NSFP/ SM7A22NSU/SM7A22NSUB

N-Channel Enhancement Mode MOSFET

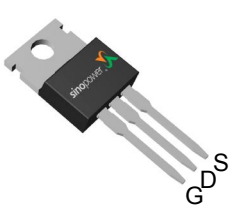
Features

- 700V/4A,
  $R_{DS(ON)}$= 1.7Ω(max.) @ V_{GS}= 10V
  V_{DS}@Tj, max=800V (typ.)
- 100% UIS + R_g Tested
- Reliable and Rugged
- Avalanche Rated
- Lead Free and Green Devices Available (RoHS Compliant)

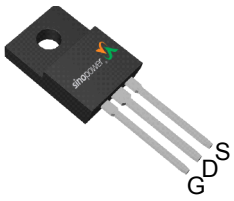
Applications

- AC/DC Power Conversion in Switched Mode Power Supplies (SMPS).
- Uninterruptible Power Supply (UPS),
- Adapter.

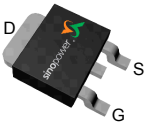
Pin Description



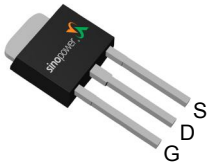
TO-220



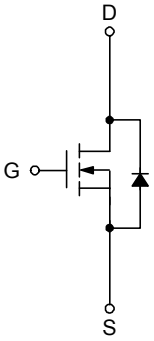
TO-220FP



TO-252-2



TO-251



N-Channel MOSFET

Ordering and Marking Information

SM7A22NS □□□-□□□

- Assembly Material
- Handling Code
- Temperature Range
- Package Code

Package Code
F : TO-220 / FP : TO-220FP / U : TO-252-2 / UB : TO-251
Operating Junction Temperature Range
C : -55 to 150 °C
Handling Code
TU : Tube (TO-220 / TO-220FP / TO-251)
TR : Tape & Reel (TO-252-2)
Assembly Material
G : Halogen and Lead Free Device

SM7A22NS F/FP/U/UB :

SM7A22NS
XXXXX

XXXXX - Lot Code

Note: SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V_{DSS}	Drain-Source Voltage		700	V
V_{GSS}	Gate-Source Voltage		±30	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	
I_S	Diode Continuous Forward Current		4 [a]	A
I_{DP}	Pulse Drain Current Tested	T_C=25°C	10 [b]	
I_D	Continuous Drain Current	T_C=25°C	4 [a]	
		T_C=100°C	2.5 [a]	
P_D	Maximum Power Dissipation for TO-220/TO-252-2/TO-251	T_C=25°C	73.5	W
		T_C=100°C	29.4	
P_D	Maximum Power Dissipation for TO-220FP	T_C=25°C	20.8	
		T_C=100°C	8.3	
$R_{\theta JC}$	Thermal Resistance-Junction to Case for TO-220/TO-252-2/TO-251		1.7	°C/W
$R_{\theta JC}$	Thermal Resistance-Junction to Case for TO-220FP		6	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		62.5	
Drain-Source Avalanche Ratings				
dv/dt [c]	MOSFET dv/dt ruggedness		50	V/ns
E_{AS} [d]	Avalanche Energy, Single Pulsed		17.5	mJ
I_{AR} [e]	Avalanche Current		0.5	A
E_{AR} [e]	Repetitive Avalanche Energy		0.06	mJ

Note a：limited by maximum junction temperature.
Note b：Bond wire current limit.
Note c：V_{DS}=560V, I_D=4A.
Note d：I_D=0.5A, V_{DD}=50V, T_j=25°C.
Note e：Repetitive Rating : Pulse width limited by maximum junction temperature.

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Electrical Characteristics (T_A = 25°C Unless Otherwise Noted)

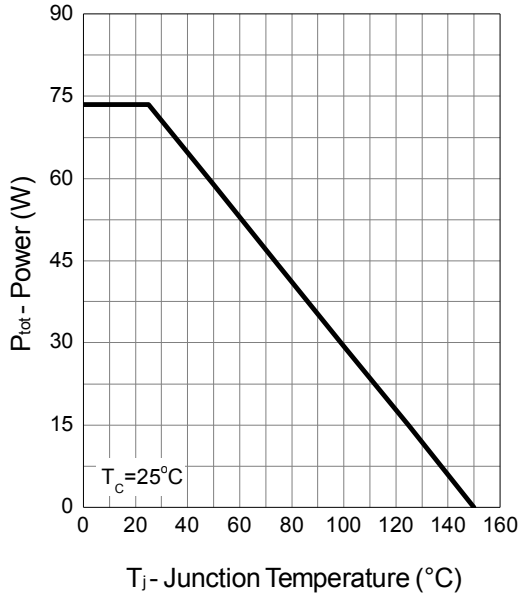
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	700	-	-	V
		T_J=150°C	-	800	-	
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=560V, V_{GS}=0V	-	-	1	μA
		T_J=150°C	-	-	200	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	2.5	3.5	4.5	V
I_{GSS}	Gate Leakage Current	V_{GS}=±30V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$ [f]	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=1A	-	1.45	1.7	Ω
Diode Characteristics						
V_{SD} [f]	Diode Forward Voltage	I_{SD}=4A, V_{GS}=0V	-	0.95	1.3	V
t_{rr}	Reverse Recovery Time	I_{SD}=4A, V_R=420V, dI_{SD}/dt=100A/μs	-	140	-	ns
Q_{rr}	Reverse Recovery Charge		-	0.85	-	μC
I_{rm}	Peak Reverse Recovery Current		-	9.5	-	A
Dynamic Characteristics [g]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V, F=1MHz	-	4	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=25V, Frequency=1.0MHz	-	230	300	pF
C_{oss}	Output Capacitance		-	195	-	
C_{rss}	Reverse Transfer Capacitance		-	1.4	-	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=400V, R_L=100Ω, I_{DS}=4A, V_{GEN}=10V, R_G=6Ω	-	11	-	ns
T_r	Turn-on Rise Time		-	21	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	16	-	
T_f	Turn-off Fall Time		-	12	-	
Gate Charge Characteristics [g]						
Q_g	Total Gate Charge	V_{DS}=560V, V_{GS}=10V, I_{DS}=1A	-	13	17	nC
Q_{gs}	Gate-Source Charge		-	3.1	-	
Q_{gd}	Gate-Drain Charge		-	5	-	

Note f : Pulse test ; pulse width≤300μs, duty cycle≤2%.
Note g : Guaranteed by design, not subject to production testing.

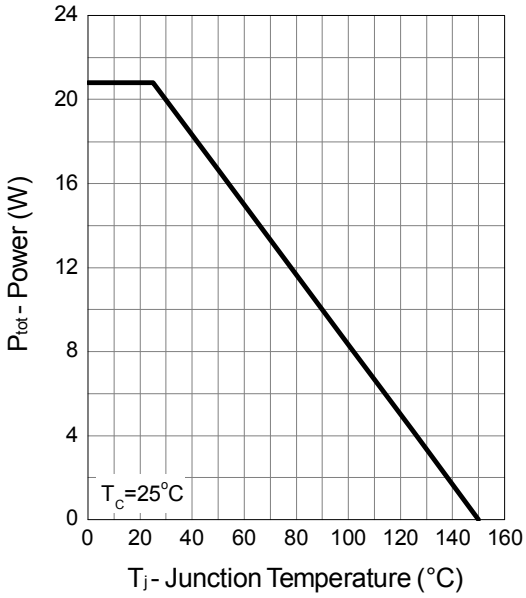
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Typical Operating Characteristics

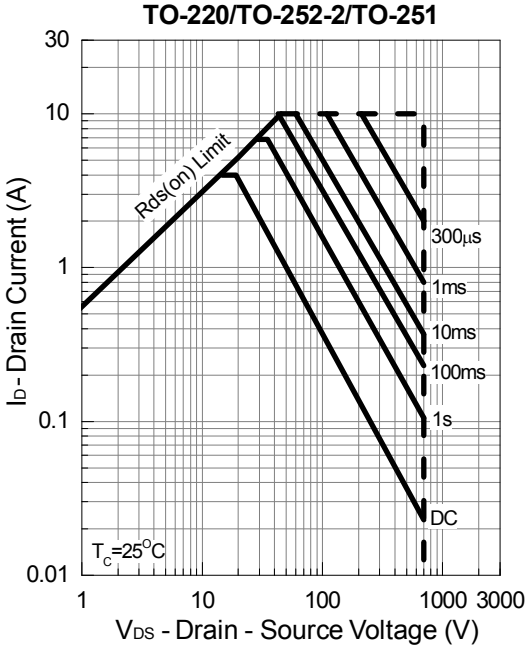
Power Dissipation : TO-220/TO-252-2/TO-251



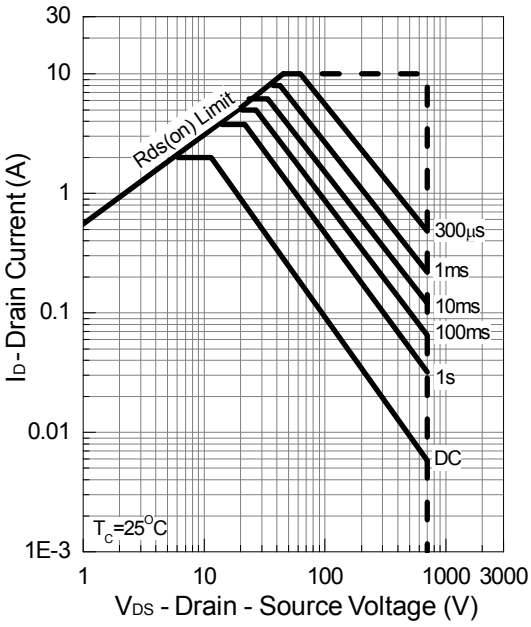
Power Dissipation : TO-220FP



Safe Operation Area : TO-220/TO-252-2/TO-251



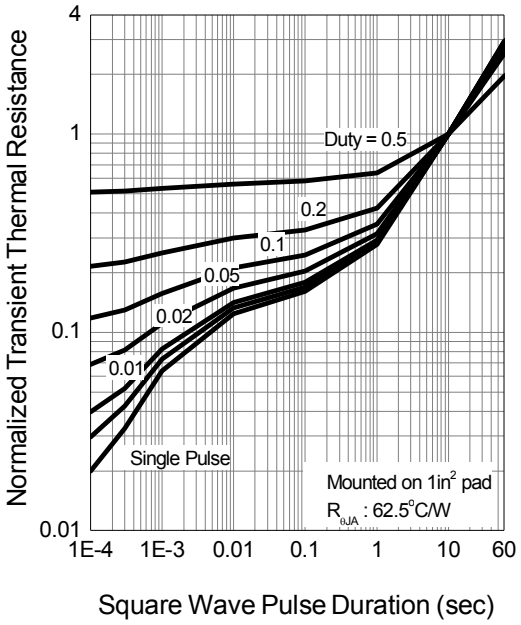
Safe Operation Area : TO-220FP



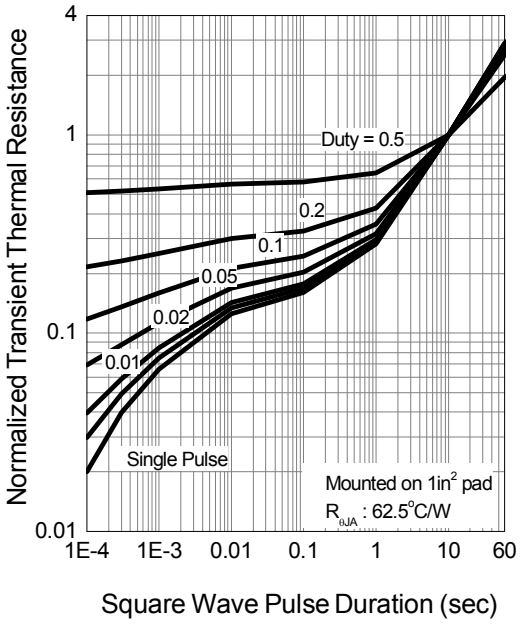
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Typical Operating Characteristics (Cont.)

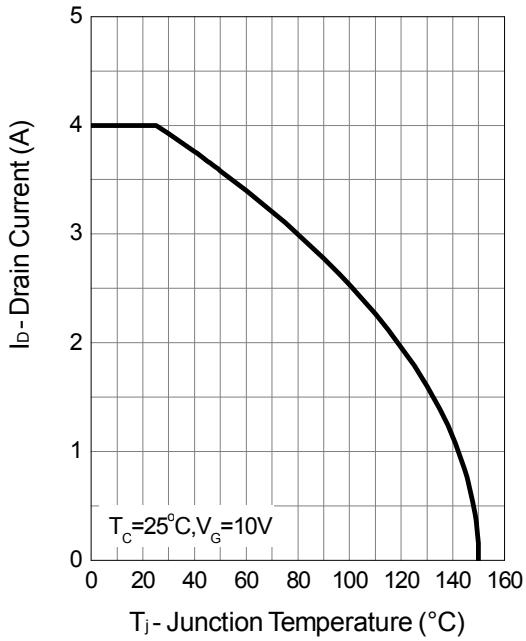
Thermal Transient Impedance: TO-220/TO-252-2/TO-251



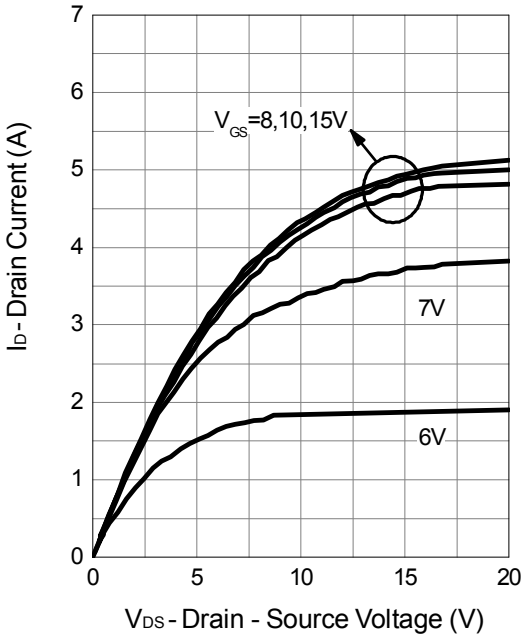
Thermal Transient Impedance: TO-220FP



Drain Current



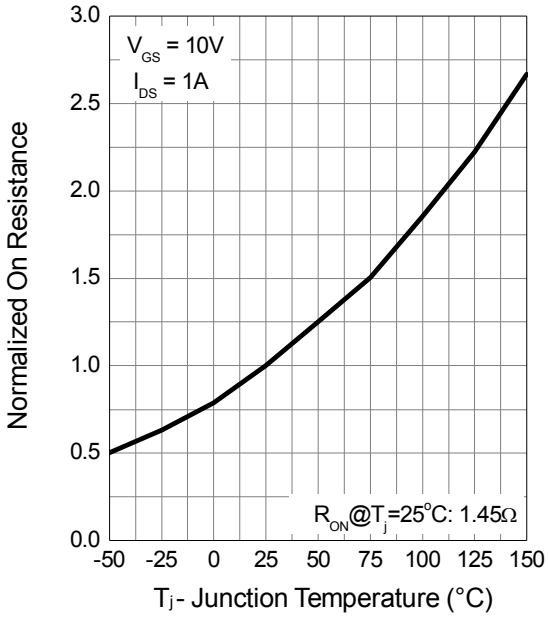
Output Characteristics



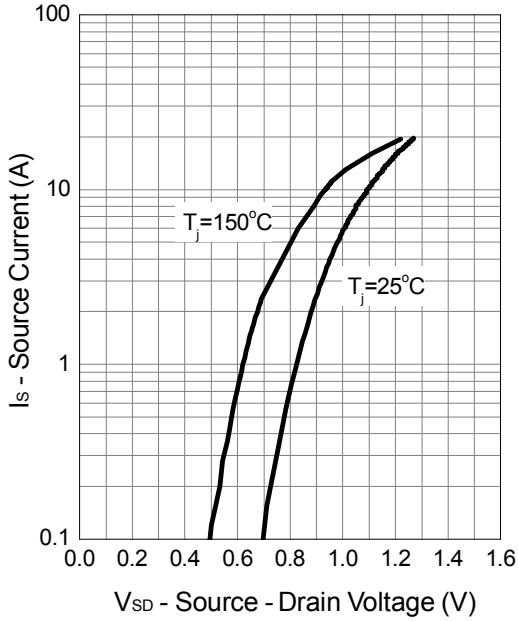
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Typical Operating Characteristics (Cont.)

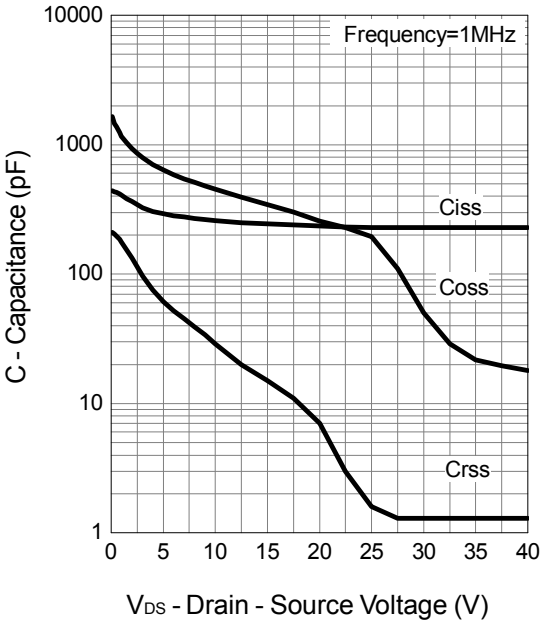
Drain-Source On Resistance



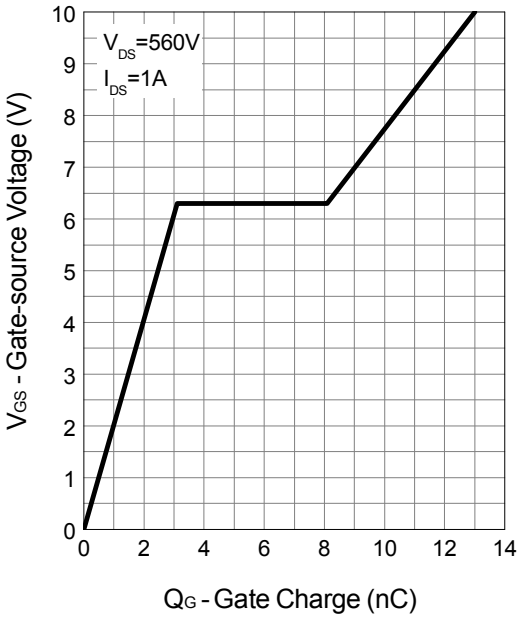
Source-Drain Diode Forward



Capacitance

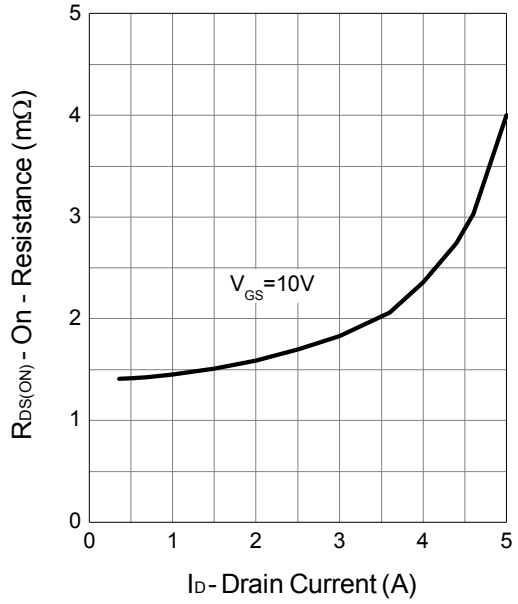


Gate Charge

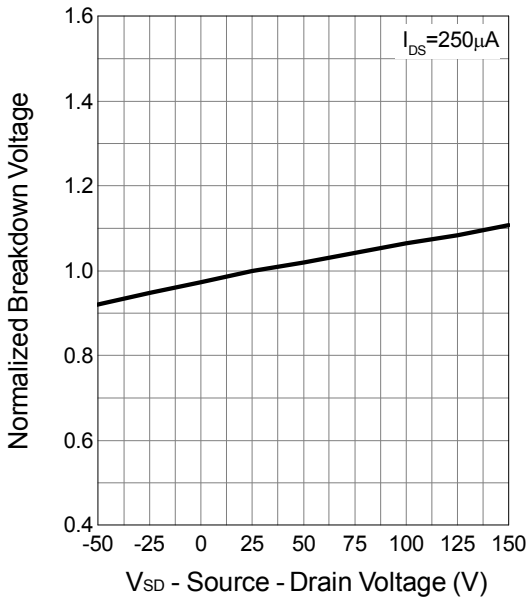


Typical Operating Characteristics (Cont.)

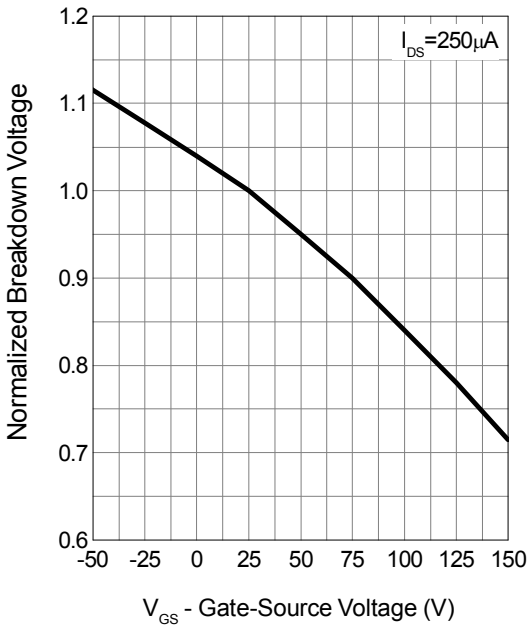
Drain-Source On Resistance



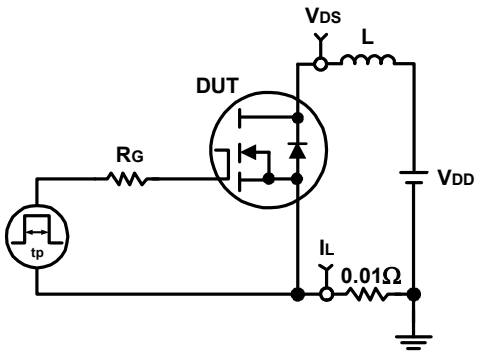
BVDSS vs Junction Temperature

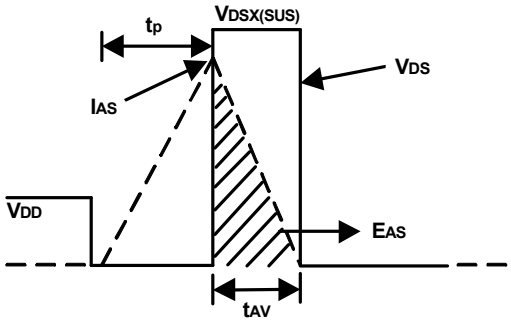


$V_{GS(th)}$ vs Junction Temperature

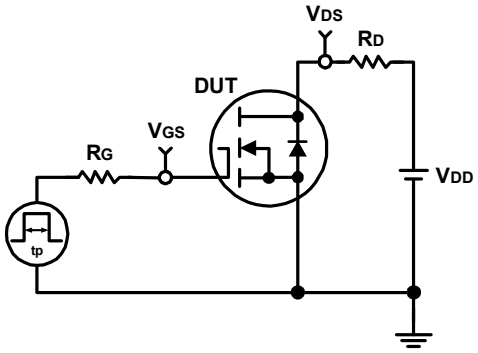


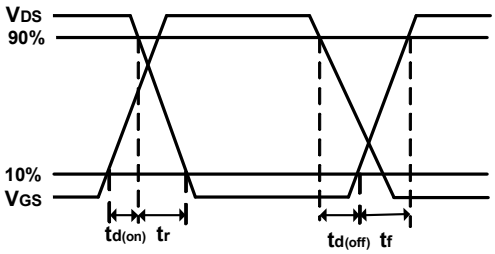
Avalanche Test Circuit and Waveforms





Switching Time Test Circuit and Waveforms





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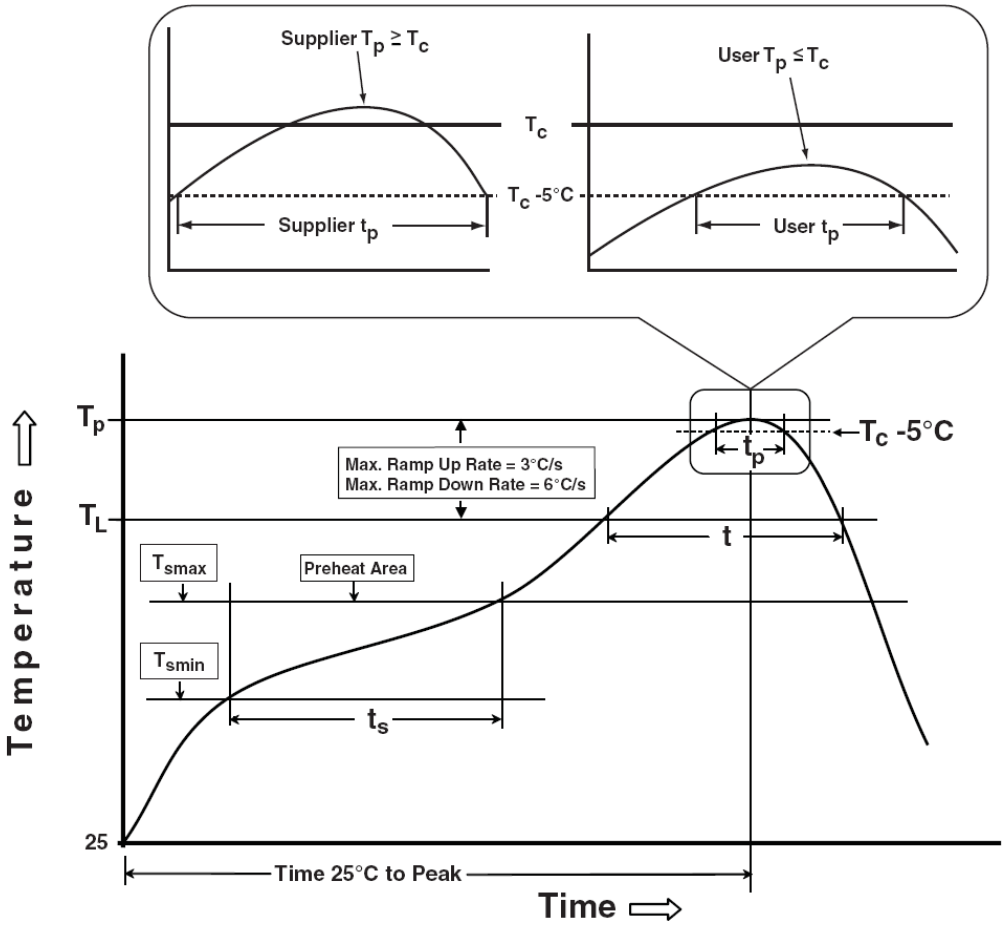
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Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	 100 °C 150 °C 60-120 seconds	 150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_P)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm^3 <350	Volume mm^3 ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm^3 <350	Volume mm^3 350-2000	Volume mm^3 >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ Tjmax
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ Tjmax
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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